

1. Scope :

This specification applies to N/P/N silicon zener double diodes chips,
Device NO. SD-00611GNL

2. Structure :

- 2-1. Planar type : N/P/N.
- 2-2. Electrodes :
 - Top side : Gold pad.
 - Back side : Gold layer.

3. Size :

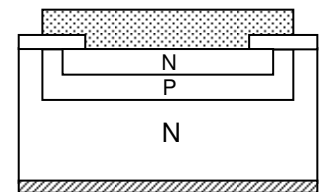
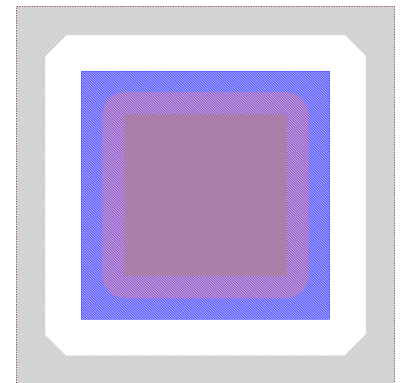
- 3-1. ^{※1}Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
- 3-2. Chip thickness : 6.0 ± 1.0 mils (0.150 ± 0.025 mm).
- 3-3. Bonding pad : 4.5 mils x 4.5 mils (0.115 mm x 0.115 mm) .
- 3-4. Pattern drawing : Refer to the attached drawing.

^{※1}Including scribing line. The chip size is about $(0.150 \pm 0.015)^2 \text{mm}^2$ after dicing.

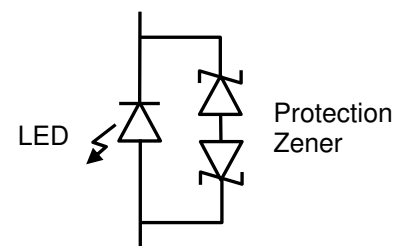
^{※2}The bonding pad dimension is $(0.110 \pm 0.010)^2 \text{mm}^2$.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Leakage Current	I _{df}	V=5V E _e =0mW/cm ²			500	nA
	I _{dr}	V=5V E _e =0mW/cm ²			500	
Zener Voltage	V _z (forward)	I _{zf} =5mA E _e =0mW/cm ²	5.2		8.0	V
	V _z (reverse)	I _{zr} =5mA E _e =0mW/cm ²	8.0		13.0	



Equivalent Circuit



5. Annotation :

- 5-1. Parallel with one LED
- 5-2. Single pad (one wire bonding applied only)
- 5-3. Double direction Zener diode protection